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Doping patterns in N-type high temperature superconductors PLCCO and NCCO

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Abstract

It has been demonstrated that the correlation between the doping distance and the critical transition temperature T_c for P-type HTSCs also applies to double doped N-type HTSCs. It is suggested that electron doped HTSCs also form superconducting current channels lying parallel in the CuO₂ plane.

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1. Introduction

Most of the high temperature superconductors (HTSC) are hole-doped compounds based on copper oxide and iron oxide. Shortly after the discovery of hole-doped HTSCs, another copper oxide family was discovered in which the carriers are electrons instead of holes [1,2]. These HTSCs with the chemical formulas $Pr_{1-\Delta}LaCe_{\Delta}CuO_{4-\delta}$ and $Ln_{2-\Delta}Ce_{\Delta}CuO_{4-\delta}$ are Ce^{4+} -doped compounds, where Ln stands for lanthanides Pr, Nd, La, Sm and Eu having transition temperatures T_c below 30K. Their undoped parent compounds PrLaCuO₄ and e.g. Nd₂CuO₄ have a so-called

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T'-phase crystal structure (Fig. 1). Compared to holedoped HTSCs, the *T'*-structure has no apical O-atom above and/or below the CuO₂-plane and cannot be doped with holes. This has been confirmed by measurements of negative Hall and negative Seebeck coefficients [3]. Both P-type and N-type HTSCs are working with an effective mass of $M_{\rm eff} = 2m_{\rm e}$.

In this paper we will analyse if electron-doped single layer (n = 1) cuprates also follow the correlation of Eq. (1) between the doping structure value $(2x)^2$ and T_c [4,5]. We have chosen the N-type cuprates $Pr_{1-\Delta}LaCe_{\Delta}CuO_{4-\delta}$ (PLCCO) and $Nd_{2-\Delta}Ce_{\Delta}CuO_{4-\delta}$ (NCCO) with Ce^{4+} doping and oxygen deficiency, because they have been studied in great detail.

$$(2x)^{2} \cdot n^{-2/3} \cdot 2M_{\rm eff} \cdot \pi k T_{\rm c} = h^{2}$$
(1)

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Fig. 1. PLCCO and NCCO are N-type HTSCs and have a T'-phase unit cell. One Nd-atom in NCCO or Pr-atom in PLCCO can be substituted by a Ce-atom in the second or fourth layer of the unit cell.

2. Double doping in cuprates

The double doping concept has been described in the case of oxygen excess and additional atoms like Y-atoms and La-atoms [3], so we will use the same procedure for the case of oxygen deficiency. The oxygen deficiency contribution is given by δ , its density by $(\Sigma_1)^{-1}$, the number of unit areas per doping atom within the CuO₂ plane by Σ_1 and the density distance by x_1 ; the extra atom contribution is given by Δ , $(\Sigma_2)^{-1}$ and x_2 , respectively. The resulting double doping is given by $(\Sigma_3)^{-1}$ and x_3 representing positions with unit cells containing both. It is a point matching for the two doping patterns projected into the superconducting plane, as illustrated in Fig. 2, leading to

$$(z_1^2 + z_2^2) \cdot (z_5^2 + z_6^2) = (z_3^2 + z_4^2) \cdot (z_7^2 + z_8^2)$$
$$= (z_9^2 + z_{10}^2)$$
(2)

The process of oxygen reduction creates oxygen vacancies in stoichiometric CuO_2 planes for PLCCO and NCCO and injecting mobile electrons into the superconducting CuO_2 layer [6]. Therefore, we project the density distribution of the Ce^{4+} -ions into the CuO_2 plane and the doped unit areas in Fig. 2 represent a complete chemical formula which is half of a unit cell.



Fig. 2. Superconducting CuO₂ plane of PLCCO (a = b = 0.398 nm). The distance between double doped unit cells is the superconducting resonance length x = 5.63 nm. The superconducting unit area has the size of $200 \cdot \text{CuO}_2$ unit areas.

has a tetragonal unit cell (space group I4/mmm) with the dimensions a = b = 0.398 nm and c = 1.227 nm(Fig. 1) which consists of $2 \cdot [Pr_{1-A}LaCe_{A}CuO_{4-\delta}]$. Using single crystals, a transition temperature in the range of $T_c = 22 \pm 2$ K has been reported by many research groups when optimizing the doping concentration of cerium and oxygen deficiency to $\Delta = 0.12$ and $\delta = 0.04$ [6–10], respectively.

The N-type HTSC material $Pr_{1-4}LaCe_4CuO_{4-\delta}$

3. Pr_{0.88}LaCe_{0.12}CuO_{3.96} (PLCCO)

The transition temperatures T_c for PLCCO and NCCO are considered to be taken at half of the transition when analysing the resistivity-temperature curves. The variation of e.g. $\pm 2 \text{ K}$ for PLCCO represents the spread/deviation of different experimental results when using single crystals only. For very thin superconducting films the transition temperature could be about 1K higher or lower depending on the substrate material for the films.

The parent compound PrLaCuO₄ is not superconducting, because the electronic arrangement $Pr^{3+}+La^{3+}+Cu^{2+}+4O^{2-}$ does not contain Cu^{3+} -ions, as is the case for most of the P-type cuprates. When doping with Ce-atoms, the electronic arrangement of the unit cell, where the Pr-atom has been replaced by a Ce-atom, is $La^{3+}+Ce^{4+}+Cu^{1+}+4O^{2-}$ and provides no superconductivity either. The Cu²⁺ is transformed into Cu¹⁺ because the preferred ionization for cerium is Ce⁴⁺, the result of the 4f¹5d¹6s² electron configuration and the lower ionization energy compared to Cu³⁺. Additional "doping" with oxygen deficiency results in a unit cell with a Ce-atom and a missing O-atom and an electronic arrangement of $La^{3+}+Ce^{4+}+Cu^{1+}+3O^{2-}+2e^{-}$ which provides two free electrons and transforms the material into a N-type HTSC.

An oxygen deficiency with $4-\delta = 3.960$ [7,8] results in a uniform doping with positions where an oxygen atom is missing with $(\Sigma_1)^{-1} = (1 - 3.960/4.0) \equiv 1\%$ and $\Sigma_1 = 100 = 10^2 + 0^2 = (z_1^2 + z_2^2)$. Superconductivity shows up at an optimized ratio of cerium to praseodymium at $\Delta = 0.12$ with $(\Sigma_2)^{-1} = 0.12/1.0$ $\equiv 12\%$ and $\Sigma_2 = 8.3 \approx 8.0 = (z_3^2 + z_4^2) = 2^2 + 2^2 \equiv$ 12.5% of Ce-atoms. Therefore, the distance between two N-type positions with two extra electrons is given by $x_3 = \sqrt{200 \cdot a} = 14.14 \cdot 0.398 \,\text{nm} = 5.63 \,\text{nm}$, where $\Sigma_3 = 200$ is the smallest common denominator of $\Sigma_1 = 100$ and $\Sigma_2 = 8$, as illustrated in Fig. 2. The calculated transition temperature $T_{\rm c}$ (calc) = 21.9 K according to Eq. (1) with n = 1 compares well with the experimental value of $T_c = 22 \pm 2 \text{ K}$ (Table 1).

xperimental and calculated trans	sition temperat	ures in double doped	I PLCC	O and NC	CO high temperat	ture supe	rconductor	s.		
Aaterial	$T_{\rm C}$ (K)	Crystal structure	Oxygei	n deficienc	sy distance	Atomi	c doping		Carrier distance x_3	$(2x_3)^2 \times 10^{-18}$
	cyp.		δ	$(\Sigma_1)^{-1}$ (%)	<i>x</i> 1 (nm)	∇	$(\Sigma_2)^{-1}$ (%)	<i>x</i> ₂ (nm)		(111)
$r_{1-A}LaCe_ACuO_{4-\delta}PLCCO$	22 ± 2	a = 0.398	0.04	1	3.98	0.12	12.5	1.13	5.63 *	127
dd _{1.85} Ce _{0.15} CuO _{4-δ} NCCO-21	21.4 ± 0.5	a = 0.394 a = 0.394 a = 1.207	0.02	0.48	5.68	0.15	<i>T.T</i>	1.42	$ASC = 200 \cdot CuO_2$ 5.68 $A_{22} = -708 \cdot CuO_2$	129
ظا, 84 Ce0.16 CuO4−∂ NCCO-22	22.3 ± 0.5	c = 1.207 a = 0.394 c = 1.207	0.02	0.50	5.57	0.16	8.0	1.39	$ASC = 200 \cdot CuO_2$ 5.57 $ASC = 200 \cdot CuO_2$	124

21.5

22.4

4. $Nd_{2-\Delta}Ce_{\Delta}CuO_{4-\delta}$ (NCCO)

The compound Nd₂CuO₄ has the same tetragonal unit cell as PLCCO with cell parameters a = 0.394 nm and $c = 1.207 \,\mathrm{nm}$ (Fig. 1) and becomes superconducting by Ce-substitution at Nd-sites when samples are properly annealed under reduced atmosphere. Several authors propose that heat treatment removes oxygen atoms at apical sites in as-grown samples, resulting in an injection of additional carriers by removing O^{-2} ions with an electronic arrangement of $Nd^{3+}+Ce^{4+}+Cu^{1+}+3O^{2-}+2e^{-}$. This provides two free electrons and transforms the material into a N-type HTSC. It has been observed that there is an abrupt onset and subsequent disappearance of superconductivity when the concentration of mobile electrons created by an oxygen deficiency is between $0.01 < \delta < 0.04$ [3,11–13]. The maximum transition temperature has been achieved at $\delta = 0.02$, which results in a uniform doping of missing oxygen atoms to $(\Sigma_1)^{-1} = (1 - 3.98/4.0) \equiv 0.5\%$ and $\Sigma_1 = 200 = 10^2 + 10^2 = (z_1^2 + z_2^2)$. The value Σ_1 could be slightly higher or lower, but must be equal to the sum of two square numbers and must match the Ce-atom content according to Eq. (2).

Most of the published T_c values are in the range of 21.5–22.7 K by using a Ce-atom contribution of $\Delta = 0.15-0.16$ leading to a doping density between 7.5% and 8%.

For $\Delta = 0.15$ we have $(\Sigma_2)^{-1} = 0.15/2.00 \equiv 7.5\%$ with $\Sigma_2 = 13.3 \approx 13 = 2^2 + 3^2 = (z_3^2 + z_4^2)$ and a doping distance of $x_2 = \sqrt{13} \cdot a = 1.42$ nm. To match the oxygen deficiency the following requirement needs to be fulfilled: $(z_3^2 + z_4^2) \cdot (z_7^2 + z_8^2) \approx 200$. There is only one solution for a given Δ with $(2^2 + 3^2) \cdot (4^2 + 0^2) = 208 = (8^2 + 12^2)$ which results in an oxygen deficiency of 0.48% and is within the accuracy of the oxygen value. This leads to a doping distance of $x_3 = \sqrt{208} \cdot a = 5.68$ nm and a calculated transition temperature of $T_c = 21.5$ K.

For $\Delta = 0.16$ we have $(\Sigma_2)^{-1} = 0.16/2.00 \equiv 8.0\%$ with $\Sigma_2 = 12.5 = 2.5^2 + 2.5^2 = (z_3^2 + z_4^2)$ and a doping distance of $x_2 = \sqrt{12.5 \cdot a} = 1.39$ nm. In this case the distance can also be in multiples of half the unit cell size because we do not know if an Nd-atom in the second or fourth layer of the unit cell will be substituted by a Ce-atom. To match the oxygen deficiency the following requirement needs to be fulfilled: $(z_3^2 + z_4^2) \cdot (z_7^2 + z_8^2) \approx 200$. Again, there is only one solution for a given Δ with $(2.5^2 + 2.5^2) \cdot (4^2 + 0^2) = 200 = (10^2 + 10^2)$ which results



Fig. 3. Superconducting unit areas of NCCO in the CuO₂ plane (a = b = 0.394 nm). (a) For NCCO-21 the distance between double doped unit cells is the superconducting resonance length x = 5.68 nm. The superconducting unit area has the size of $208 \cdot \text{CuO}_2$ unit areas. (b) For NCCO-22 the superconducting resonance length is x = 5.57 nm and the superconducting unit area has the size of $200 \cdot \text{CuO}_2$ unit areas.

in an oxygen deficiency of 0.50%. This leads to a doping distance of $x_3 = \sqrt{200 \cdot a} = 5.57$ nm and a calculated transition temperature of $T_c = 22.4$ K.

The Ce-atom content was not investigated with high accuracy by most of the authors. Therefore, we have illustrated both cases in Fig. 3 and refer for $\Delta = 0.16$ to $T_c = 22.3$ K [14] and for $\Delta = 0.15$ to $T_c = 21.5$ K [15] and $T_c = 21.3$ [16].

5. Discussion

The experimental T_c values of N-type HTSCs match the correlation curve of Eq. (1) for P-type HTSCs very closely (Fig. 4). The correlation curve has a slope of $m_1 = 2.77 \times 10^{-15} \text{ m}^2 \text{ K}$ and an ordinate value of $+0.2 \times 10^{-18} \text{ m}^2$. These results support the resonance concept for HTSCs with an effective mass of $M_{\text{eff}} = 2m_e$ and carrying a charge of $Q = 2e^-$. Also for N-type HTSCs, superconducting charge carriers seem to be organized in parallel current channels or stripes within the CuO₂-plane. It is interesting to note that the superconducting unit area pattern of PLCCO (Fig. 2) has a strong similarity to the single-crystal X-ray diffraction mesh scans in [6], which should be investigated further.



Fig. 4. Crystal geometry factor $(2x)^2$ of the superconducting plane versus the inverse critical transition temperature of different P- and N-type HTSCs. The value x is the doping distance and n represents the number of superconducting planes per chemical formula in the unit cell containing Cu³⁺-ions in cuprates or Fe²⁺-ions in iron-based HTSCs.

References

- Y. Tokura, H. Takagi, S. Uchida, A superconducting copper oxide compound with electrons as the charge carriers, Nature 337 (1989) 345–347.
- [2] M. Fujita, T. Kubo, S. Kuroshima, T. Uefuji, K. Kawashima, K. Yamada, Magnetic and superconducting phase diagram of electron-doped Pr_{1-x}LaCe_xCuO₄, Physical Review B 67 (2003) 014514.
- [3] H. Takagi, S. Uchida, Y. Tokura, Superconductivity produced by electron doping in CuO₂-layered compounds, Physical Review Letters 62 (10) (1989) 1197–1200.
- [4] H.P. Roeser, F. Hetfleisch, F.M. Huber, M.F. von Schoenermark, M. Stepper, A. Moritz, A.S. Nikoghosyan, Correlation between oxygen excess density and critical transition temperature in superconducting Bi-2201, Bi-2212 and Bi-2223, Acta Astronautica 63 (2008) 1372–1375.
- [5] H.P. Roeser, F.M. Huber, M.F. von Schoenermark, A.S. Nikoghosyan, High temperature superconducting with two doping atoms in La-doped Bi-2201 and Y-doped Bi-2212, Acta Astronautica (2008), accepted for publication.
- [6] H.J. Kang, P. Dai, B.J. Campbell, P.J. Chupas, S. Rosenkranz, P.L. Lee, Q. Huang, S. Li, S. Komiya, Y. Ando, Microscopic annealing process and its impact on superconductivity in *T'*structure electron-doped copper oxides, Nature Materials 6 (2007) 224–229.
- [7] H.J. Kang, P. Dai, H.A. Mook, D.N. Argyriou, V. Sikolenko, J.W. Lynn, Y. Kurita, S. Komiya, Y. Ando, Electronically competing phases and their magnetic field dependence

in electron-doped nonsuperconducting and superconducting $Pr_{0.88}LaCe_{0.12}CuO_4$ \pm $_{\delta}, Physical Review B 71 (2005) 214512.$

- [8] S.D. Wilson, S. Li, P. Dai, W. Bao, J.H. Chung, H.J. Kang, S.H. Lee, S. Komiya, Y. Ando, Q. Si, Evolution of low-energy spin dynamics in the electron-doped high-transition-temperature superconductor Pr_{0.88}LaCe_{0.12}CuO_{4-δ}, Physical Review B 74 (2006) 144514.
- [9] S.D. Wilson, P. Dai, S. Li, S. Chi, H.J. Kang, J.W. Lynn, Resonance in the electron-doped high-transition-temperature superconductor $Pr_{0.88}LaCe_{0.12}CuO_{4-\delta}$, Nature 442 (2006) 59–62.
- [10] P. Dai, H.J. Kang, H.A. Mook, M. Matsuura, J.W. Lynn, Y. Kurita, S. Komiya, Y. Ando, Electronic inhomogeneity and competing phases in electron-doped superconducting $Pr_{0.88}LaCe_{0.12}CuO_{4-\delta}$, Physical Review B 71 (2005) 100502(R).
- [11] S.J. Collocott, R. Driver, C. Andrikidis, Specific heat and magnetic susceptibility of superconducting and semiconducting $Nd_{1.85}Ce_{0.15}CuO_{4-\delta}$, Physical Review B 45 (2) (1992) 945–950.
- [12] K. Kurahashi, H. Matsushita, M. Fujita, K. Yamada, Heat treatment effects on the superconductivity and crystal structure of Nd_{1.85}Ce_{0.15}CuO₄ studied using a single crystal, Journal of Physical Society of Japan 71 (3) (2002) 910–915.
- [13] M. Suzuki, S. Kubo, K. Ishiguro. K. Haruna, Hall coefficient for oxygen-reduced Nd_{2-x}Ce_xCuO_{4- δ}, Physical Review B 50 (1994) 9434–9438.
- [14] Y. Hidaka, M. Suzuki, Growth and anisotropic superconducting properties of Nd_{2-x}Ce_xCuO_{4-ν}, Nature 338 (1989) 635–637.

- [15] J.S. Kim, D.R. Gaskel, The phase stability diagrams for the systems $Nd_2CuO_{4-\delta}$ and $Nd_{1.85}Ce_{0.15}CuO_{4-\delta}$, Physica C 209 (1993) 381–388.
- [16] C. Fanggao, A. Al-Kheffaji, P.J. Ford, D.A. Ladds, J. Freestone, B. Chapman, L. Manosa, D.P. Almond, G.A. Saunders,

A comparative study of the high- T_c electron superconductor Nd_{1.85}Ce_{0.15}CuO_{4-y}, and its parent compound Nd₂CuO_{4-y}, Superconductor Science and Technology 3 (1990) 422–428.